

# RENESAS TECHNICAL UPDATE

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Product Category	MPU/MCU		Document No.	TN-RA*-A0025A/E	Rev.	1.00
Title	RA4M2 Group, Change of 48QFN permission junction temperature		Information Category	Technical Notification		
Applicable Product	RA4M2 Group	Lot No.	Reference Document	RA4M2 Group User's Manual Hardware Rev.1.10		
		All				

Permissible junction temperature of RA4M2 48QFN was changed.

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Before

**Table 47.3 DC characteristics**

Conditions: Products with operating temperature ( $T_a$ ) -40 to +105°C

Parameter	Symbol	Typ	Max	Unit	Test conditions
Permissible junction temperature	$T_j$	—	125	°C	High-speed mode Low-speed mode Subosc-speed mode
			115		

Note: Make sure that  $T_j = T_a + \theta_{ja} \times \text{total power consumption (W)}$ , where total power consumption =  $(V_{CC} - V_{OH}) \times \Sigma I_{OH} + V_{OL} \times \Sigma I_{OL} + I_{CCmax} \times V_{CC}$ .

After

**Table 47.3 DC characteristics**

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